Bruce W Wessels

List of Publications by Year in Descending Order

249 papers	7,301 citations	41 h-index	76 g-index
253 ext. papers	8,108 ext. citations	4.6 avg, IF	5.84 L-index

#	Paper	IF	Citations
249	Photoluminescence spectroscopy of excitonic emission in CsPbCl3 perovskite single crystals. *Journal of Luminescence*, **2022**, 243, 118661	3.8	2
248	CsPbBr3 perovskite detectors with 1.4% energy resolution for high-energy □rays. *Nature Photonics*, **2021**, 15, 36-42	33.9	79
247	Demonstration of Energy-Resolved □Ray Detection at Room Temperature by the CsPbCl Perovskite Semiconductor. *Journal of the American Chemical Society*, **2021**, 143, 2068-2077	16.4	18
246	Inorganic Halide Perovskitoid TlPbI3 for Ionizing Radiation Detection. *Advanced Functional Materials*, **2021**, 31, 2006635	15.6	7
245	Excitons in CsPbBr Halide Perovskite. *Journal of Physical Chemistry Letters*, **2021**, 12, 9301-9307	6.4	2
244	Direct thermal neutron detection by the 2D semiconductor LiInPSe. *Nature*, **2020**, 577, 346-349	50.4	21
243	Monte Carlo simulation of transport properties in wide gap Hg3Se2I2. *Semiconductor Science and Technology*, **2019**, 34, 115003	1.8	1
242	Purification and Improved Nuclear Radiation Detection of Tl6SI4 Semiconductor. *Crystal Growth and Design*, **2019**, 19, 4738-4744	3.5	1
241	Controlling the Vapor Transport Crystal Growth of Hg3Se2I2 Hard Radiation Detector Using Organic Polymer. *Crystal Growth and Design*, **2019**, 19, 2074-2080	3.5	5
240	From 0D Cs3Bi2I9 to 2D Cs3Bi2I6Cl3: Dimensional Expansion Induces a Direct Band Gap but Enhances Electron□Phonon Coupling. *Chemistry of Materials*, **2019**, 31, 2644-2650	9.6	72
239	Perovskites with a Twist: Strong In1+ Off-Centering in the Mixed-Valent CsInX3 (X = Cl, Br). *Chemistry of Materials*, **2019**, 31, 9554-9566	9.6	18
238	Carrier recombination mechanism in CsPbBr3 revealed by time-resolved photoluminescence spectroscopy. *Physical Review B*, **2019**, 100,	3.3	10
237	Noise sources and their limitations on the performance of compound semiconductor hard radiation detectors. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2019**, 916, 133-140	1.2	4
236	Perovskite CsPbBr3 single crystal detector for alpha-particle spectroscopy. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2019**, 922, 217-221	1.2	51
235	High spectral resolution of gamma-rays at room temperature by perovskite CsPbBr single crystals. *Nature Communications*, **2018**, 9, 1609	17.4	246
234	An Effective Purification Process for the Nuclear Radiation Detector Tl6SeI4. *Crystal Growth and Design*, **2018**, 18, 3484-3493	3.5	7
233	CuISe: A Metal-Inorganic Framework Wide-Bandgap Semiconductor for Photon Detection at Room Temperature. *Journal of the American Chemical Society*, **2018**, 140, 1894-1899	16.4	11

232	Particle Detection and Charge Transport Characteristics in the A3M2I9 Defect Perovskites (A = Cs, Rb; M = Bi, Sb). *ACS Photonics*, **2018**, 5, 3748-3762	6.3	61
231	Role of Stoichiometry in the Growth of Large Pb2P2Se6 Crystals for Nuclear Radiation Detection. *ACS Photonics*, **2018**, 5, 566-573	6.3	11
230	Dynamic Disorder, Band Gap Widening, and Persistent Near-IR Photoluminescence up to At Least 523 K in ASnI3 Perovskites (A = Cs+, CH3NH3+ and NH2CH?NH2+). *Journal of Physical Chemistry C*, **2018**, 122, 26353-26361	3.8	17
229	Deep Level and Near-Band-Edge Recombination in Semiconducting Antiperovskite Hg3Se2I2 Single Crystals. *Advanced Optical Materials*, **2018**, 6, 1800328	8.1	2
228	Resolving the Energy of Ray Photons with MAPbI3 Single Crystals. *ACS Photonics*, **2018**, 5, 4132-4138	6.3	67
227	Defect Antiperovskite Compounds HgQI (Q = S, Se, and Te) for Room-Temperature Hard Radiation Detection. *Journal of the American Chemical Society*, **2017**, 139, 7939-7951	16.4	38
226	Strong ElectronPhonon Coupling and Self-Trapped Excitons in the Defect Halide Perovskites A3M2I9 (A = Cs, Rb; M = Bi, Sb). *Chemistry of Materials*, **2017**, 29, 4129-4145	9.6	344
225	TlSn2I5, a Robust Halide Antiperovskite Semiconductor for Ray Detection at Room Temperature. *ACS Photonics*, **2017**, 4, 1805-1813	6.3	30
224	Charge Transport and Observation of Persistent Photoconductivity in TlSeI Single Crystals. *Journal of Physical Chemistry Letters*, **2017**, 8, 1538-1544	6.4	13
223	TlSbS2: a Semiconductor for Hard Radiation Detection. *ACS Photonics*, **2017**, 4, 2891-2898	6.3	8
222	Electronic defects in the halide antiperovskite semiconductor Hg3Se2I2. *Physical Review B*, **2017**, 96,	3.3	3
221	Improved Crystal Growth of Tl6SeI4 for Ray Detection Material by Oxide Impurity Removal. *Crystal Growth and Design*, **2017**, 17, 6096-6104	3.5	6
220	$chi ^{(2)}$ Modulator With 40-GHz Modulation Utilizing BaTiO3 Photonic Crystal Waveguides. *IEEE Journal of Quantum Electronics*, **2017**, 53, 1-10	2	16
219	Cascaded spintronic logic with low-dimensional carbon. *Nature Communications*, **2017**, 8, 15635	17.4	27
218	Photoluminescence fatigue and inhomogeneous line broadening in semi-insulating Tl6SeI4single crystals. *Semiconductor Science and Technology*, **2016**, 31, 065009	1.8	14
217	Integrated BaTiO3 modulator with 8 dB extinction at 50 GHz and 25 km reach **2016**,		1
216	An Unusual Crystal Growth Method of the Chalcohalide Semiconductor, Hg3S2Cl2: A New Candidate for Hard Radiation Detection. *Crystal Growth and Design*, **2016**, 16, 2678-2684	3.5	13
215	Charge Transport Mechanisms in a Pb2P2Se6 Semiconductor. *ACS Photonics*, **2016**, 3, 1877-1887	6.3	5

214	Refined Synthesis and Crystal Growth of Pb2P2Se6 for Hard Radiation Detectors. *Crystal Growth and Design*, **2016**, 16, 5100-5109	3.5	9
213	Charge Transport in Magnetic Semiconductor p-n Heterojunctions. *IEEE Transactions on Electron Devices*, **2015**, 62, 2470-2474	2.9	4
212	Magnetism and Mn Clustering in (In,Mn)Sb Magnetic Semiconductors. *ACS Applied Materials & Interfaces*, **2015**, 7, 24159-67	9.5	15
211	High-field magnetic circular dichroism in ferromagnetic InMnSb and InMnAs: Spin-orbit-split hole bands and g factors. *Physical Review B*, **2015**, 92,	3.3	7
210	Excitonic emissions and above-band-gap luminescence in the single-crystal perovskite semiconductors CsPbBr3 and CsPbCl3. *Physical Review B*, **2015**, 92,	3.3	194
209	Mn doped InSb studied at the atomic scale by cross-sectional scanning tunneling microscopy. *Applied Physics Letters*, **2015**, 107, 222102	3.4	1
208	Bilayer avalanche spin-diode logic. *AIP Advances*, **2015**, 5, 117102	1.5	4
207	Hard Radiation Detection from the Selenophosphate Pb2P2Se6. *Advanced Functional Materials*, **2015**, 25, 4874-4881	15.6	25
206	Emitter-Coupled Spin-Transistor Logic: Cascaded Spintronic Computing Beyond 10 GHz. *IEEE Journal on Emerging and Selected Topics in Circuits and Systems*, **2015**, 5, 17-27	5.2	7
205	Characterization of deep level defects in Tl6I4S single crystals by photo-induced current transient spectroscopy. *Journal Physics D: Applied Physics*, **2015**, 48, 075303	3	2
204	Emitter-coupled spin-transistor logic. *Journal of Parallel and Distributed Computing*, **2014**, 74, 2461-2469	4.4	5
203	Investigation of Semi-Insulating Cs2Hg6S7 and Cs2Hg6-xCdxS7 Alloy for Hard Radiation Detection. *Crystal Growth and Design*, **2014**, 14, 5949-5956	3.5	10
202	Crystal Growth of Tl4CdI6: A Wide Band Gap Semiconductor for Hard Radiation Detection. *Crystal Growth and Design*, **2014**, 14, 2401-2410	3.5	30
201	Photo-induced current transient spectroscopy of single crystal Tl6I4Se. *Semiconductor Science and Technology*, **2014**, 29, 115002	1.8	5
200	Optical investigation of defects in semi-insulating Tl6I4S single crystals. *Physical Review B*, **2014**, 90,	3.3	6
199	High-performance computing based on spin-diode logic **2014**,		1
198	Cs2MIIMIV3Q8 (Q = S, Se, Te): An Extensive Family of Layered Semiconductors with Diverse Band Gaps. *Chemistry of Materials*, **2013**, 25, 3344-3356	9.6	64
197	Photoconductivity in Tl6SI4: A Novel Semiconductor for Hard Radiation Detection. *Chemistry of Materials*, **2013**, 25, 2868-2877	9.6	39

196	Transient photocurrent measurements in alkali chalcogenide ternary compound semiconductors. *Semiconductor Science and Technology*, **2013**, 28, 015022	1.8	7
195	Crystal Growth of the Perovskite Semiconductor CsPbBr3: A New Material for High-Energy Radiation Detection. *Crystal Growth and Design*, **2013**, 13, 2722-2727	3.5	927
194	CsCdInQ3 (Q = Se, Te): New Photoconductive Compounds As Potential Materials for Hard Radiation Detection. *Chemistry of Materials*, **2013**, 25, 2089-2099	9.6	46
193	Photonic Crystal Waveguide Electro-Optic Modulator With a Wide Bandwidth. *Journal of Lightwave Technology*, **2013**, 31, 1601-1607	4	22
192	Photoconductivity in the chalcohalide semiconductor, SbSeI: a new candidate for hard radiation detection. *Inorganic Chemistry*, **2013**, 52, 7045-50	5.1	43
191	MAGNETORESISTANCE OF NARROW GAP MAGNETIC SEMICONDUCTOR HETEROJUNCTIONS. *Spin*, **2013**, 03, 1340011	1.3	
190	Cyclotron resonance in ferromagnetic InMnAs and InMnSb. *Physical Review B*, **2013**, 88,	3.3	11
189	Magnetoresistance in InMnAs/InAs heterojunctions and its dependence on alloy composition and temperature. *Applied Physics Letters*, **2013**, 103, 053503	3.4	4
188	CsHgInS3: a New Quaternary Semiconductor for γ-ray Detection. *Chemistry of Materials*, **2012**, 24, 4434-4441	9.1	50
187	Characterization of InMnSb epitaxial films for spintronics. *Journal of Physics: Conference Series*, **2012**, 371, 012032	0.3	1
186	Mercury and antimony chalcohalide semiconductors as new candidates for radiation detection applications at room temperature **2012**,		6
185	Formation of native defects in the γ-ray detector material Cs2Hg6S7. *Applied Physics Letters*, **2012**, 101, 202103	3.4	10
184	A Spin-Diode Logic Family. *IEEE Nanotechnology Magazine*, **2012**, 11, 1026-1032	2.6	18
183	Ferromagnetic InMnSb multi-phase films study by aberration-corrected (scanning) transmission electron microscopy. *Journal of Applied Physics*, **2012**, 111, 07C311	2.5	32
182	Crystal Growth and Characterization of the X-ray and γ-ray Detector Material Cs2Hg6S7. *Crystal Growth and Design*, **2012**, 12, 3250-3256	3.5	40
181	Time-resolved differential transmission in MOVPE-grown ferromagnetic InMnAs. *Physical Review B*, **2012**, 85,	3.3	10
180	InMnAs magnetoresistive spin-diode logic **2012**,		4
179	Photoluminescent properties of semiconducting Tl6I4Se. *Semiconductor Science and Technology*, **2012**, 27, 015016	1.8	5

178	Emitter-coupled spin-transistor logic **2012**,		3
177	Investigation of defect levels in Cs2Hg6S7 single crystals by photoconductivity and photoluminescence spectroscopies. *Journal of Applied Physics*, **2012**, 112, 063702	2.5	10
176	Structural and magnetic properties of epitaxial In1−xMnxSb semiconductor alloys with x > 0.08. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 032801	1.3	5
175	Dimensionally reduced heavy atom semiconductors as candidate materials for y-ray detection: the case of Cs2Hg6S7. *Materials Research Society Symposia Proceedings*, **2011**, 1341, 1		3
174	Thallium Chalcogenide-Based Wide-Band-Gap Semiconductors: TlGaSe2 for Radiation Detectors. *Chemistry of Materials*, **2011**, 23, 3120-3128	9.6	79
173	Thallous chalcogenide (Tl6I4Se) for radiation detection at X-ray and γ-ray energies. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2011**, 659, 333-335	1.2	19
172	Thallium chalcohalides for X-ray and γ-ray detection. *Journal of the American Chemical Society*, **2011**, 133, 10030-3	16.4	98
171	Dimensional reduction: a design tool for new radiation detection materials. *Advanced Materials*, **2011**, 23, 4163-7	24	147
170	Spin-dependent magnetotransport in a p-InMnSb/n-InSb magnetic semiconductor heterojunction. *Applied Physics Letters*, **2011**, 98, 193506	3.4	20
169	Alkali Metal Chalcogenides for Radiation Detection. *Materials Research Society Symposia Proceedings*, **2011**, 1341, 1		3
168	Cyclotron resonance in InMnAs and InMnSb ferromagnetic films. *Journal of Physics: Conference Series*, **2011**, 334, 012056	0.3	2
167	Local electronic and magnetic structure of mixed ferrite multilayer materials. *Physical Review B*, **2010**, 81,	3.3	9
166	Strain-driven spin reorientation in magnetite/barium titanate heterostructures. *Applied Physics Letters*, **2010**, 96, 092510	3.4	32
165	Using the infrared magnetorefractive effect to compare the magnetoresistance in (100) and (111) oriented Fe3O4 films. *Journal of Applied Physics*, **2010**, 107, 09B102	2.5	9
164	High-temperature ferromagnetism in epitaxial (In,Mn)Sb films. *Physical Review B*, **2010**, 81,	3.3	22
163	Magnetoamplification in a bipolar magnetic junction transistor. *Physical Review Letters*, **2010**, 105, 117202	7.4	35
162	Magnetotransport properties of InMnSb magnetic semiconductor thin films. *Physical Review B*, **2010**, 82,	3.3	44
161	Ferroelectric Thin Film Microcavities and their Optical Resonant Properties. *Materials Research Society Symposia Proceedings*, **2009**, 1182, 24		

160	Polarization reversal and backswitching dynamics in epitaxial BaTiO3 thin films. *Journal of Applied Physics*, **2009**, 106, 054113	2.5	18
159	Giant magnetoresistance of magnetic semiconductor heterojunctions. *Physical Review B*, **2009**, 79,	3.3	25
158	Electronic structure of substitutional Mn in epitaxial In0.965Mn0.035Sb film. *Applied Physics Letters*, **2009**, 95, 201905	3.4	7
157	Ferromagnetic semiconductors and the role of disorder. *New Journal of Physics*, **2008**, 10, 055008	2.9	28
156	Highly efficient broadband second harmonic generation using polydomain epitaxial barium titanate thin film waveguides. *Applied Physics Letters*, **2008**, 92, 221103	3.4	15
155	Magnetocapacitance effect in InMnAs□InAs p-n heterojunctions. *Journal of Vacuum Science & Technology B*, **2008**, 26, 1526		3
154	Interfacial structure and chemistry of epitaxial CoFe2O4 thin films on SrTiO3 and MgO substrates. *Applied Physics Letters*, **2008**, 93, 181901	3.4	38
153	Dynamic response of polydomain ferroelectric barium titanate epitaxial thin films and its field dependence. *Journal of Applied Physics*, **2008**, 104, 064115	2.5	8
152	Dependence of magnetic circular dichroism on doping and temperature in In1□MnxAs epitaxial films. *Physical Review B*, **2007**, 76,	3.3	14
151	Ferroelectric Epitaxial Thin Films for Integrated Optics. *Annual Review of Materials Research*, **2007**, 37, 659-679	12.8	125
150	Epitaxial growth and strain relaxation of BaTiO3 thin films on SrTiO3 buffered (001) Si by molecular beam epitaxy. *Journal of Vacuum Science & Technology B*, **2007**, 25, 1053		36
149	Phase stability of heteroepitaxial polydomain BaTiO3 thin films. *Journal of Materials Research*, **2007** , 22, 1384-1389	2.5	5
148	Bragg Reflector Waveguide and Electro-Optic Modulator Based on Barium Titanate Epitaxial Thin Films. *Materials Research Society Symposia Proceedings*, **2007**, 1014, 1		
147	Simulation and Fabrication of Two Dimensional Nonlinear Photonic Crystals using Barium Titanate Thin Films. *Materials Research Society Symposia Proceedings*, **2007**, 1014, 1		1
146	Epitaxial growth and strain relaxation of MgO thin films on Si grown by molecular beam epitaxy. *Journal of Vacuum Science & Technology B*, **2006**, 24, 2586		25
145	Evidence of room temperature sp-d exchange in InMnAs epitaxial films. *Applied Physics Letters*, **2006**, 89, 102505	3.4	9
144	High-field magnetoresistance in p-(In,Mn)As□-InAs heterojunctions. *Applied Physics Letters*, **2006**, 88, 072105	3.4	26
143	BaTiO3 thin-film waveguide modulator with a low voltage-length product at near-infrared wavelengths of 0.98 and 1.55 microm. *Optics Letters*, **2005**, 30, 254-6	3	37

142	Investigation of composition fluctuations in GaN:Mg using optical transmission spectroscopy, near-field scanning optical microscopy, and scanning Kelvin probe microscopy. *Journal of Applied Physics*, **2005**, 98, 023513	2.5	11
141	Low temperature deposition of epitaxial BaTiO3 films in a rotating disk vertical MOCVD reactor. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 1674		15
140	Local environment of ferromagnetically ordered Mn in epitaxial InMnAs. *Applied Physics Letters*, **2005**, 86, 072505	3.4	16
139	Optical investigation of electronic states of Mn4+ ions in p-type GaN. *Applied Physics Letters*, **2005**, 86, 042505	3.4	26
138	Negative magnetoresistance in (In,Mn)As semiconductors. *Physical Review B*, **2004**, 70,	3.3	32
137	Optical properties of Mn4+ ions in GaN:Mn codoped with Mg acceptors. *Applied Physics Letters*, **2004**, 84, 5320-5322	3.4	27
136	Three Dimensional Domain Structure in Epitaxial Barium Titanate Thin Films. *Journal of Electroceramics*, **2004**, 13, 89-93	1.5	13
135	Thin Film Ferroelectrics for Guided Wave Devices. *Journal of Electroceramics*, **2004**, 13, 135-138	1.5	8
134	Integration of MgO on Si(001) Using SrO and SrTiO3 Buffer Layers by Molecular Beam Epitaxy. *Journal of Electroceramics*, **2004**, 13, 149-154	1.5	6
133	Phonon-assisted deep level luminescence in heavily Mg-doped InGaN. *Journal of Electronic Materials*, **2004**, 33, 431-435	1.9	3
132	Local structure around Mn atoms in room-temperature ferromagnetic (In,Mn)As thin films probed by extended x-ray absorption fine structure. *Applied Physics Letters*, **2004**, 84, 481-483	3.4	45
131	Low-voltage, polarization-insensitive, electro-optic modulator based on a polydomain barium titanate thin film. *Applied Physics Letters*, **2004**, 85, 4615-4617	3.4	55
130	Electrooptic modulation up to 40 GHz in a barium titanate thin film waveguide modulator. *Optics Express*, **2004**, 12, 5962-7	3.3	69
129	Blue emission band in compensated GaN:Mg codoped with Si. *Physical Review B*, **2003**, 68,	3.3	29
128	Nanosecond-Scale Domain Dynamics in BaTiO 3 Probed by Time-Resolved X-Ray Diffraction. *Ferroelectrics*, **2003**, 290, 115-124	0.6	5
127	Dielectric properties of plasma-spray-deposited BaTiO3 and Ba0.68Sr0.32TiO3 thick films. *Journal of Materials Research*, **2003**, 18, 1227-1231	2.5	9
126	Relative dielectric constant of epitaxial BaTiO3 thin films in the GHz frequency range. *Applied Physics Letters*, **2003**, 83, 5274-5276	3.4	33
125	Phase stability of epitaxial KTaxNb1⊠O3 thin films deposited by metalorganic chemical vapor deposition. *Journal of Materials Research*, **2003**, 18, 106-110	2.5	15

124	Dynamic response of the dielectric and electro-optic properties of epitaxial ferroelectric thin films. *Physical Review B*, **2002**, 65,	3.3	23
123	Optical properties of the deep Mn acceptor in GaN:Mn. *Applied Physics Letters*, **2002**, 80, 1731-1733	3.4	134
122	Dielectric properties of epitaxial KNbO3 ferroelectric thin films. *Journal of Materials Research*, **2002** , 17, 275-278	2.5	21
121	Ferromagnetism in (In,Mn)As diluted magnetic semiconductor thin films grown by metalorganic vapor phase epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1582		29
120	Deep Donor-Acceptor Pair Luminescence in Codoped GaN. *Materials Research Society Symposia Proceedings*, **2002**, 743, L5.8.1		1
119	Interfacial Layer Effects in Ba1-xSrxTiO3 Thick Films prepared by Plasma Spray. *Materials Research Society Symposia Proceedings*, **2002**, 758, 271		2
118	Diffuse Phase Transition in Epitaxial BaTiO3 Thin Films. *Journal of Materials Research*, **2002**, 17, 669-674	2.5	20
117	Fast time-resolved x-ray diffraction in BaTiO3 films subjected to a strong high-frequency electric field. *Applied Physics Letters*, **2002**, 80, 3159-3161	3.4	22
116	Growth and characterization of OMVPE grown (In,Mn)As diluted magnetic semiconductor. *Journal of Electronic Materials*, **2001**, 30, 1408-1411	1.9	46
115	Electrical properties of p-type GaN:Mg codoped with oxygen. *Applied Physics Letters*, **2001**, 78, 222-224	3.4	78
114	Comparative optical studies of p-type and unintentionally doped GaN: The influence of annealing. *Applied Physics Letters*, **2001**, 78, 58-60	3.4	12
113	Erbium-Doped Barium Titanate Thin Film Waveguides for Integrated Optical Amplifiers. *Materials Research Society Symposia Proceedings*, **2001**, 688, 1		3
112	Erbium-Doped Barium Titanate Thin Film Waveguides for Integrated Optical Amplifiers. *Materials Research Society Symposia Proceedings*, **2001**, 694, 1		
111	Dielectric Properties of Spray Deposited BaTiO3 and Ba0.68Sr0.32TiO3. *Materials Research Society Symposia Proceedings*, **2001**, 698, 361		2
110	Metalorganic Molecular Beam Epitaxy of Magnesium Oxide on Silicon. *Materials Research Society Symposia Proceedings*, **2000**, 619, 149		6
109	Epitaxial Ferroelectric BaTiO3 Thin Films for Microphotonic Applications. *Materials Research Society Symposia Proceedings*, **2000**, 637, E1.9.1		7
108	Deep Level Formation in Undoped and Oxygen-Doped GaN. *Materials Research Society Symposia Proceedings*, **2000**, 639, 11561		
107	Photoluminescence Studies of p-type GaN:Mg Co-doped with Oxygen. *Materials Research Society Symposia Proceedings*, **2000**, 639, 6391		2

106	MOCVD of Epitaxial BaTiO3 Films Using a Liquid Barium Precursor. *Chemical Vapor Deposition*, **2000**, 6, 175-177		30
105	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via Dip-Pen Nanolithography and Wet Chemical Etching. *Advanced Materials*, **2000**, 12, 1600-1603	24	113
104	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 301-307		6
103	Photoluminescence band near 2.9 eV in undoped GaN epitaxial layers. *Journal of Applied Physics*, **2000**, 87, 3351-3354	2.5	93
102	Optical Study of GaN Doped with Mn Grown by Metal Organic Vapor Phase Epitaxy. *Materials Research Society Symposia Proceedings*, **2000**, 639, 371		4
101	Investigation of the formation of the 2.8 eV luminescence band in p-type GaN:Mg. *Applied Physics Letters*, **2000**, 76, 3011-3013	3.4	99
100	Pressure dependence of the blue luminescence in Mg-doped GaN. *Applied Physics Letters*, **2000**, 77, 2536-2538	3.4	5
99	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via Dip-Pen Nanolithography and Wet Chemical Etching **2000**, 12, 1600		2
98	Defect Luminescence in Heavily Mg Doped GaN. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 968-973		3
97	Dynamic response of the electro-optic effect in epitaxial KNbO3. *Applied Physics Letters*, **1999**, 75, 2707-2709	3.4	22
96	Behavior of 2.8- and 3.2-eV photoluminescence bands in Mg-doped GaN at different temperatures and excitation densities. *Physical Review B*, **1999**, 59, 13176-13183	3.3	205
95	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. *Materials Research Society Symposia Proceedings*, **1999**, 595, 1		3
94	Luminescence Efficiency of Erbium-Doped BaTiO3 Thin Films. *Materials Research Society Symposia Proceedings*, **1999**, 597, 15		2
93	Dynamic Response of the Electro-Optic Effect in Epitaxial Ferroelectric Thin Films. *Materials Research Society Symposia Proceedings*, **1999**, 597, 157		5
92	Growth of MgO by Metal-Organic Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1999**, 606, 45		4
91	Dielectric properties of epitaxial BaTiO3 thin films. *Applied Physics Letters*, **1998**, 73, 2248-2250	3.4	112
90	Luminescence quenching in Er-doped BaTiO3 thin films. *Applied Physics Letters*, **1998**, 73, 1625-1627	3.4	29
89	Defect Luminescence in Heavily Mg Doped GaN. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		

88	Strain in Epitaxial BaTiO3 Thin Films Prepared by MOCVD. *Materials Research Society Symposia Proceedings*, **1998**, 541, 489		1
87	Epitaxial KNbo3 and its Nonlinear Optical Properties. *Materials Research Society Symposia Proceedings*, **1998**, 541, 741		1
86	Morphological stability of strained-layer semiconductors. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1997**, 15, 1056		28
85	Thin-film channel waveguide electro-optic modulator in epitaxial BaTiO3. *Applied Physics Letters*, **1997**, 71, 1783-1785	3.4	106
84	Carbon–hydrogen complexes in vapor phase epitaxial GaN. *Applied Physics Letters*, **1997**, 70, 357-359	3.4	56
83	Hydrogen complexes in epitaxial BaTiO3 thin films. *Applied Physics Letters*, **1997**, 71, 327-329	3.4	15
82	The Effects Of Substrate Thermal Mismatch on the Domain Structure of MOCVD-Derived Potassium Niobate Thin Films. *Materials Research Society Symposia Proceedings*, **1997**, 474, 31		1
81	Epitaxial Ferroelectric Oxides for Electro-Optic and Non-Linear Optical Applications. *Materials Research Society Symposia Proceedings*, **1997**, 495, 23		1
80	The Effects of Domain Structure on the Electro-Optic Response of Potassium Niobate Thin Films. *Materials Research Society Symposia Proceedings*, **1996**, 453, 259		6
79	Rare-Earth Doped Epitaxial InGaP and its Optical Properties. *Materials Research Society Symposia Proceedings*, **1996**, 422, 247		3
78	Excitation Properties of Er-Doped GaP from Photoluminescence and High Pressure Studies. *Materials Research Society Symposia Proceedings*, **1996**, 422, 279		2
77	1.54 μm Electroluminescence from Erbium Doped Gallium Phosphide Diodes. *Materials Research Society Symposia Proceedings*, **1996**, 422, 345		2
76	Deep Level Defects in Mg-Doped GaN. *Materials Research Society Symposia Proceedings*, **1996**, 423, 525		4
75	Defects and Electronic Transport in Rare Earth Doped Epitaxial SrTiO3 Thin Films. *Materials Research Society Symposia Proceedings*, **1996**, 433, 21		1
74	The Morphological Stability of Strained Epitaxial Layers. *Materials Research Society Symposia Proceedings*, **1996**, 440, 335		
73	The Optical Properties of Channel Waveguides in Batio3 Thin Films. *Materials Research Society Symposia Proceedings*, **1996**, 446, 349		2
72	Electroluminescence from forward-biased Er-doped GaP p-n junctions at room temperature. *Applied Physics Letters*, **1996**, 68, 1126-1128	3.4	7
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